

Data Sheet N2582, REV.-

S6D02065A S6D02065E



S6D02065A S6D02065E 650V SIC POWER SCHOTTKY RECTIFIERS

Description

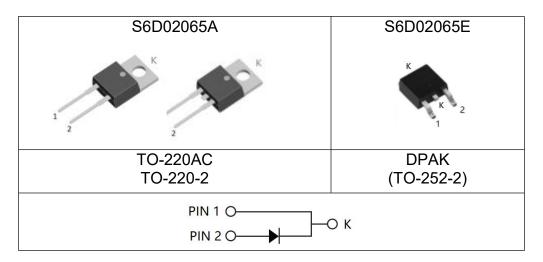
This 650V 2A diode is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S6D02065A/S6D02065E are ideal for energy sensitive, high frequency applications in challenging environments.

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request





Maximum Ratings:



Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	VRRM	-		
Working Peak Reverse Voltage	V _{RWM}		650	V
DC Blocking Voltage	V _{DC}			
Average Rectified Forward Current	IF (AV)1	T _C =25°C	12.5	A
Average received rorward ourient	I _{F (AV)2}	T _c =165°C	2	A
	I _{FRM1}	10ms, Half Sine pulse, T_c =25°C	12	A
Repetitive Peak Forward Surge Current	I _{FRM2}	10ms, Half Sine pulse, T _C =110°C	9	A
	I _{FSM1}	10ms, Half Sine pulse, T _C =25°C	20	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM2}	10ms, Half Sine pulse, T _C =110°C	15	A
	P _{tot1}	T _C =25°C	60	W
Power Dissipation	P _{tot2}	T _c =110℃	26	W

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 2A, Pulse, TJ = 25 °C	1.27	1.5	V
	V _{F2}	@ 2A, Pulse, T _J = 175 °C	1.4	1.6	V
Reverse Current at DC condition*	I _{R1}	$@V_R = rated V_R$ T _J = 25 °C	0.3	3	uA
Reverse Current *	I _{R2}	@V _R = rated V _R T _J = 175 °C	6	25	uA
Junction Capacitance	Ст	V _R =0V, T _J =25°C,f=1MHz	170	-	pF
Reverse Recovery Charge	Qc	I _F = 2A, di/dt = 200A/μs V _R = 400 V, T _J =25°C	10.60	-	nC
Capacitance Stored Energy	Ec	V _R = 400 V, T _J =25°C	2.60	-	۲ų

* Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	S6D02065A	S6D02065E	Units
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	2.5	2.4	°C/W

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Ordering Information

Device	Package	Shipping
S6D02065A	TO-220AC(TO-220-2)	50pcs /tube
S6D02065E	DPAK(TO-252-2)	3000pcs /reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.



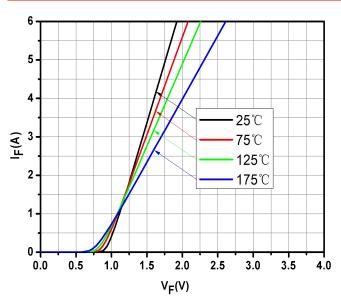
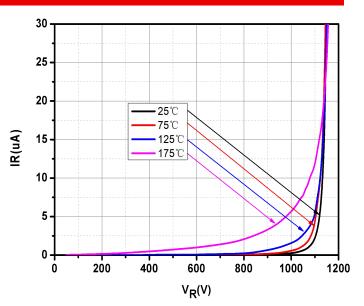
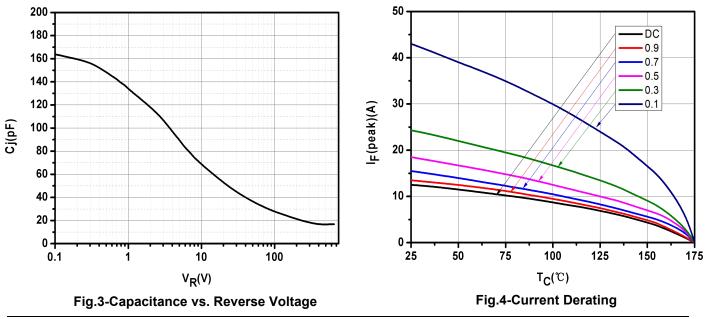


Fig.1-Typical Forward Voltage Characteristics







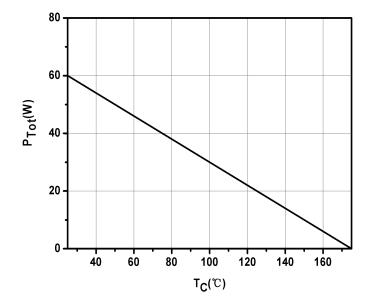
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S6D02065A



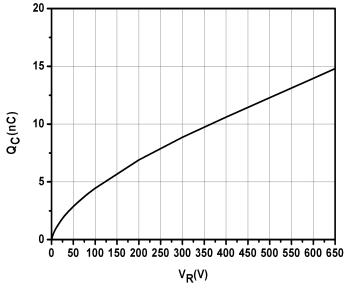


Fig.5-Power Derating

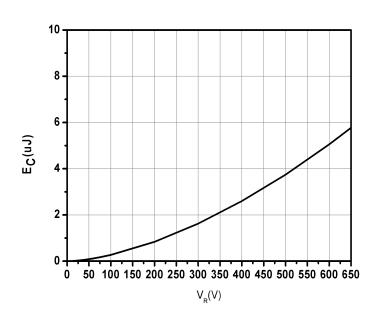


Fig.7-Capacitance Stored Energy vs. Reverse Voltage

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Fig.6-Total Capacitance Charge vs. Reverse Voltage



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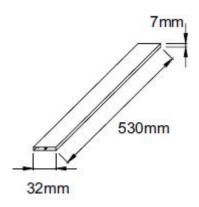
Marking Diagram

RoHS

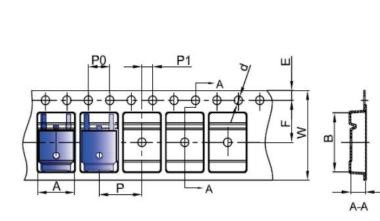
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Where XXXXX is YYWWL S6D = Device Type = Package type = Forward Current (50A) A/E 02 S6D02065E = Reverse Voltage (650V) 065 \$6D02065A SSG XXXXX SSG = SSG YΥ = Year SSG XXXXX WW = Week L = Lot Number Cautions: Molding resin Epoxy resin UL:94V-0

Tube Specification (TO-220-2)



Carrier Tape & Reel Specification



SYMBOL	Millimeters			
STMBOL	Min.	Max.		
A	6.80	7.00		
В	10.40	10.60		
С	2.60	2.80		
d	Φ1.45	Φ1.65		
E	1.65	1.85		
F	7.40	7.60		
P0	3.90	4.10		
Р	7.90	8.10		
P1	1.90	2.10		
W	15.90	16.30		

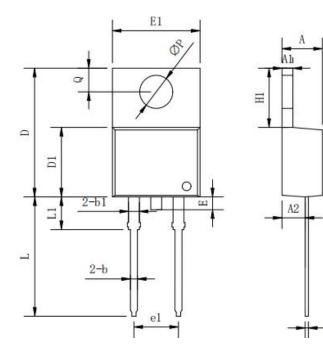


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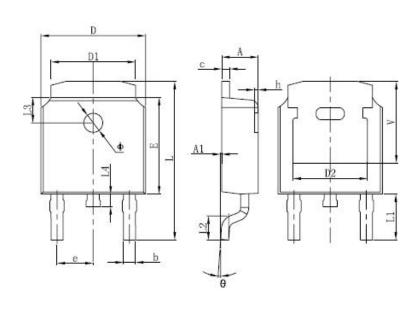


Mechanical Dimensions TO-220AC



Symbol	Dimensions in millimeters			
	Min.	Typical	Max.	
A	3.56	-	4.83	
A1	0.51	-	1.40	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
С	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E	-	-	1.78	
E1	9.65	10.16	10.67	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.70	-	14.73	
L1	-	-	6.35	
ΦΡ	-	3.56	_	
Q	2.54	-	3.43	

Mechanical Dimensions DPAK(TO-252-2)



SYMBOL	Dimensions in millimeters			
	Min.	Тур.	Max.	
A	2.18	-	2.39	
A1	-	-	0.13	
b	0.64	-	0.89	
С	0.46	-	0.89	
D	6.35	-	6.73	
D1	4.95	-	5.46	
D2	4.32	-	-	
E	5.97	6.1	6.22	
е		2.29BSC		
L	9.4	-	10.41	
L1	2.90 REF.			
L2	1.4	1.52	1.78	
L3	1.60 REF.			
L4	-	_	1.02	
Φ	1.1	-	1.3	
Θ	0°	-	10°	
V	5.21		-	

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